

REGULATING PULSE WIDTH MODULATOR

DESCRIPTION

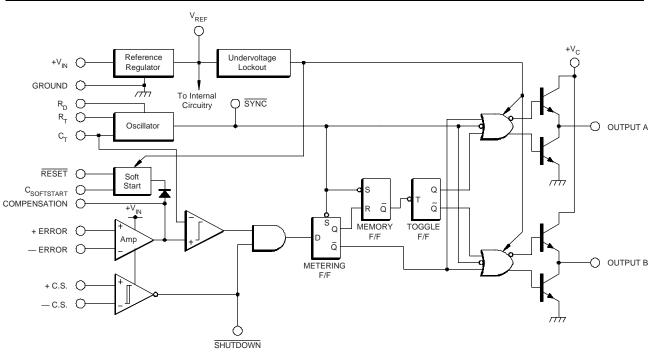
The SG1526B is a high-performance pulse width modulator for switching power supplies which offers improved functional and electrical characteristics over the industrystandard SG1526. A direct pin-for-pin replacement for the earlier device with all its features, it incorporates the following enhancements: a bandgap reference circuit for improved regulation and drift characteristics, improved undervoltage lockout, lower temperature coefficients on oscillator frequency and current-sense threshold, tighter tolerance on softstart time, much faster SHUTDOWN response, improved double-pulse supperession logic for higher speed operation, and an improved output driver design with low shoot-through current, and faster rise and fall times. This versatile device can be used to implement single-ended or push-pull switching regulators of either polarity, both transformerless and transformer-coupled. The SG1526B is specified for operation over the full military ambient temperature range of -55°C to 150°C. The SG2526B is characterized for the industrial range of -25°C to 150°C, and the SG3526B is designed for the commercial range of 0°C to 125°C.

FEATURES

- 8V to 35V Operation
- 5V Low drift 1% Bandgap Reference
- 1Hz to 500kHz Oscillator Range
- Dual 100mA Source/Sink
- Digital Current Limiting
- Double Pulse Suppression
- Programmable Deadtime
- Improved Undervoltage Lockout
- Single Pulse Metering
- Programmable Soft-start
- Wide current Limit Common Mode Range
- TTL/CMOS Compatible Logic Ports
- Symmetry Correction Capability
- Guaranteed 6 Unit Synchronization
- Shoot-through Currents Less than 100mA
- Improved Shutdown Delay
- Improved Rise and Fall Time

HIGH RELIABILITY FEATURES

- Available To MIL-STD-883, ¶ 1.2.1
- Available to DSCC Standard Microcircuit Drawing (SMD)
- MIL-M38510/12603BVA SG1526BJ-JAN
- Radiation data available.
- MSC-AMS Level "S" Processing Available



BLOCK DIAGRAM



ABSOLUTE MAXIMUM RATINGS (Note 1)

Input Voltage (V _{IN})	
Collector Supply Voltage (V _c)	40V
Logic Inputs	
Analog Inputs	0.3V to V
Source/Sink Load Current (each output)	200mÄ
Reference Load Current	50mA

Note 1. Exceeding these ratings could cause damage to the device.

THERMAL DATA

J Package:	
Thermal Resistance-Junction to Case, θ_{JC}	25°C/W
Thermal Resistance-Junction to Ambient, θ_{JA}	
N Package:	
Thermal Resistance-Junction to Case, θ_{JC}	30°C/W
Thermal Resistance-Junction to Ambient, θ_{IA}	60°C/W
DW Package:	
Thermal Resistance-Junction to Case, θ_{JC}	35°C/W
Thermal Resistance-Junction to Ambient, θ_{IA}	90°C/W
L Package:	
Thermal Resistance-Junction to Case, θ_{JC}	35°C/W
Thermal Resistance-Junction to Ambient, θ_{JA} 1	

RECOMMENDED OPERATING CONDITIONS (Note 2)

Input Voltage	8V to 35V
Collector Supply Voltage	4.5V to 35V
Sink/Source Load Current (each output)	0 to 100mA
Reference Load Current	0 to 20mA
Oscillator Frequency Range	1Hz to 500kHz
Oscillator Timing Resistor	$2k\Omega$ to $150k\Omega$

Logic Sink Current 15mA
Operating Junction Temperature
Hermetic (J, L Packages) 150°C
Plastic (N, DW Packages)150°C
Storage Temperature Range65°C to 150°C
Lead Temperature (Soldering, 10 Seconds) 300°C
RoHS Peak Package Solder Reflow Temp. (40 sec. max. exp.) 260°C (+0, -5)

Note A. Junction Temperature Calculation: $T_J = T_A + (P_D \times \theta_{JA})$.

Note B. The above numbers for θ_{JC} are maximums for the limiting thermal resistance of the package in a standard mounting configuration. The θ_{JA} numbers are meant to be guidelines for the thermal performance of the device/pc-board system. All of the above assume no ambient airflow.

Oscillator Timing Capacitor	470pF to 20μF
Available Deadtime Range at 40kHz	5% to 50%
Operating Junction Temperature Range	e:
SG1526B	55°C to 125°C
SG2526B	25°C to 85°C
SG3526B	0°C to 70°C

Note 2. Range over which the device is functional.

ELECTRICAL CHARACTERISTICS

(Unless otherwise specified, these specifications apply over the operating ambient temperatures for SG1526B with -55°C \leq T_A \leq 125°C, SG2526B with -25°C \leq T_A \leq 85°C, SG3526B with 0°C \leq T_A \leq 70°C, and V_{IN} = 15V. Low duty cycle pulse testing techniques are used which maintains junction and case temperatures equal to the ambient temperature.)

Parameter	Test Conditions	SG15	SG1526B/2526B			SG3526B		
Falailletei	Test conditions	Min.	Тур.	Max.	Min.	Тур.	Max.	Units
Reference Section (Note 3)								
Output Voltage	T ₁ = 25°C	4.95	5.00	5.05	4.90	5.00	5.10	V
Line Regulation	$V_{IN} = 8 \text{ to } 35 \text{V}$		7	10		10	20	mV
Load Regulation	$I_1 = 0$ to 20mA		10	20		10	25	mV
Temperature Stability (Note 9)	Över Operating T		15	50		15	50	mV
Total Output Voltage Range (Note 9)		4.90	5.00	5.10	4.85	5.00	5.15	V
Short Circuit Current	$V_{REF} = 0V$	25	50	125	25	50	125	mA
Undervoltage Lockout Section								
RESET Output Voltage	$V_{\text{REF}} = 3.8 V$		0.2	0.4		0.2	0.4	V
RESET Output Voltage	$V_{\text{REF}}^{\text{NET}} = 4.8 \text{V}$	2.4	4.8		2.4	4.8		V



ELECTRICAL CHARACTERISTICS (continued)

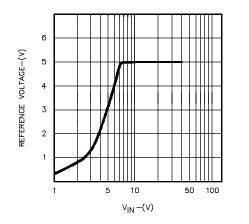
Parameter	Parameter Test Conditions SG1526B/25				G3526		Units	
Farameter	Test conditions	Min.	Тур.	Max.	Min.	Тур.	Max.	Units
Oscillator Section (Note 4)								
Initial Accuracy	$T_{I} = 25^{\circ}C$		±3	±8		±3	±8	%
Voltage Stability	V _{IN} = 8 to 35V		0.5	1.0		0.5	1.0	%
Temperature Stability (Note 9)	Over Operating T					3	5	%
Minimum Frequency (Note 9)	$R_{T} = 150 k\Omega, C_{T} = 20 \mu F$	$R_{\tau} = 150 k\Omega, C_{\tau} = 20 \mu F$ 1.0					1.0	Hz
Maximum Frequency	$R_{\tau} = 2k\Omega, C_{\tau} = 470pF$							kHz
Sawtooth Peak Voltage	$V_{IN} = 35V$	2.5	3.0	3.5	2.5	3.0	3.5	V
Sawtooth Valley Voltage	$V_{iN} = 8V$	0.5	1.0	1.1	0.5	1.0	1.1	V
SYNC Pulse Width	$R_{L} = 2.0 k\Omega$ to V_{REF}		1.0	2		1.0	2	μs
Error Amplifier Section (Note 5)		I	1			1		
Input Offset Voltage	$R_s \leq 2k\Omega$		2	5		2	10	mV
Input Bias Current			-350	-1000		-350	-2000	nA
Input Offset Current			35	100		35	200	nA
DC Open Loop Gain	$R_{_{\rm I}} \ge 10 M \Omega$	64	72		60	72		dB
High Output Voltage	V_{PIN1}^{L} - $V_{PIN2} \ge 150 \text{mV}$, $I_{SOURCE} = 100 \mu \text{A}$	3.6	4.2		3.6	4.2		V
Low Output Voltage	$V_{\text{PIN2}} - V_{\text{PIN1}} \ge 150 \text{mV}, I_{\text{SINK}} = 100 \mu \text{A}$		0.2	0.4		0.2	0.4	V
Common Mode Rejection	$R_{s}^{PINZ} \leq 2k\Omega$	70	94		70	94		dB
Supply Voltage Rejection	$V_{IN}^{s} = 8V$ to 35V	66	80		66	80		dB
PWM Comparator Section (Note	1 113		1			1		•
Minimum Duty Cycle	V _{COMPENSATION} = 0.4V			0			0	%
Maximum Duty Cycle	$V_{\text{COMPENSATION}} = 3.6 V$	45	49		45	49		%
Digital Ports (SYNC, SHUTDOW								
HIGH Output Voltage	I _{SOURCE} = 40µA	2.4	4		2.4	4		V
LOW Output Voltage	$I_{SINK} = 3.6 \text{mA}$		0.2	0.4		0.2	0.4	v
HIGH Input Current	$V_{\rm H} = 2.4 \rm V$		-125	-200		-125		μA
LOW Input Current	$V_{\mu} = 0.4V$		-225	-360		-225		μΑ
SHUTDOWN Delay to Output	(Note9)			200			200	ns
Current Limit Comparator Sect								
Sense Voltage	$R_s \le 50\Omega$	90	100	110	80	100	120	mV
Input Bias Current	N _S 2 0022	30	-3	-10	00	-3	-10	μA
Delay to Output (Note 9)				400		0	400	ns
Soft-Start Section				400			-00	113
Error Clamp Voltage	$\overline{RESET} = 0.4 V$		0.1	0.4.		0.1	0.4.	V
C _s Charging Current	$\frac{\text{RESET}}{\text{RESET}} = 2.4\text{V}$	50	100	150	50	100	150	μA
Output Drivers (each output) (N			100	100		100	100	μπ
HIGH Output Voltage	I _{SOURCE} = 20mA	12.5	13.5		12.5	13.5		V
	I _{SOURCE} = 100mA	12.0	13		12.0	13.5		V
LOW Output Voltage	I _{SURCE} = 10011A	12	0.2	0.3	12	0.2	0.3	V
2011 Output Voltage	$I_{SINK} = 100 \text{mA}$		1.2	2		1.2	2	v
Collector Leakage	$V_c = 40V$		50	150		50	150	μA
Rise Time	$C_{1} = 1000 \text{pF}$		0.3	0.4		0.3	0.4	μA μS
Fall Time	$C_{L} = 1000 \text{pF}$		0.1	0.15		0.1	0.15	μs
Power Consumption Section (N			0.1	0.10		0.1	0.10	μο
	SHUTDOWN = 0.4V		18	30		10	30	mA
Standby Current	SHUTDOWN = 0.4V		Ið	30		18	30	mA

Note 3. $I_{L} = 0mA$ Note 4. $F_{OSC} = 40kHz (R_{T} = 4.12k\Omega \pm 1\%, C_{T} = .01\mu F \pm 1\%, R_{D} = 0\Omega)$ Note 5. $V_{CM} = 0$ to 5.2V Note 6. $V_{CM} = 0$ to 12V

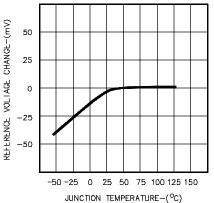
Note 7. $V_{\rm C}$ = 15V Note 8. $V_{\rm IN}$ = 35V Note 9. These parameters, although guaranteed over the recommended operating conditions, are not tested in production.



CHARACTERISTIC CURVES



REFERENCE VOLTAGE VS. SUPPLY VOLTAGE



REFERENCE TEMPERATURE STABILITY

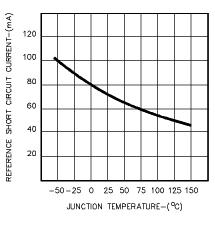
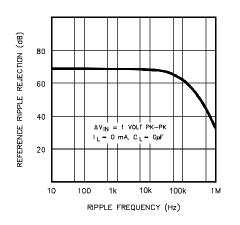
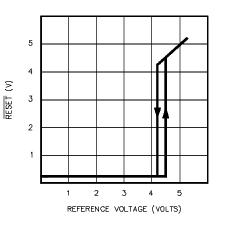


FIGURE 3. REFERENCE SHORT CIRCUIT





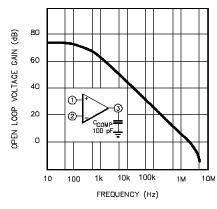


FIGURE 4. REFERENCE RIPPLE REJECTION

FIGURE 1.

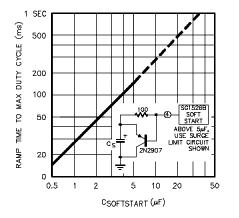




FIGURE 2.

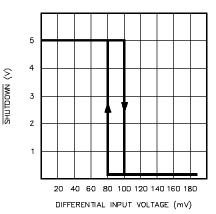


FIGURE 6. ERROR AMPLIFIER OPEN LOOP GAIN VS. FREQUENCY

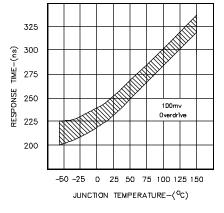


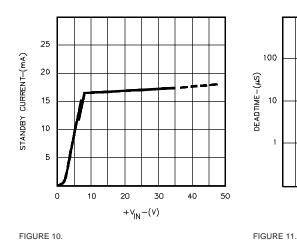
FIGURE 7. SOFTSTART TIME CONSTANT VS. C_S

FIGURE 8. CURRENT LIMIT TRANSFER FUNCTION

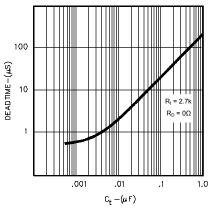
FIGURE 9. COMPARATOR INPUT TO DRIVER OUTPUT DELAY



CHARACTERISTIC CURVES (continued)



STANDBY CURRENT VS. SUPPLY VOLTAGE



OUTPUT DRIVER DEADTIME VS. C_T VALUE

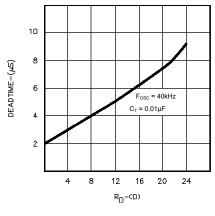
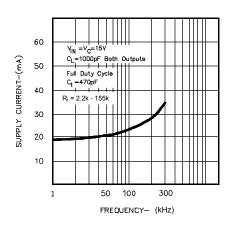
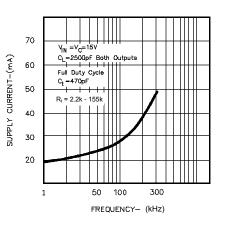


FIGURE 12. OUTPUT DRIVER DEADTIME VS. R_D VALUE





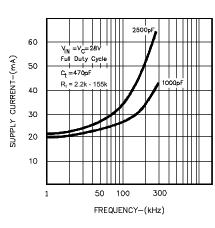
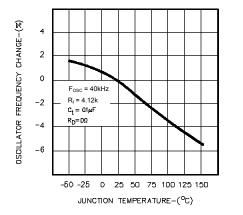
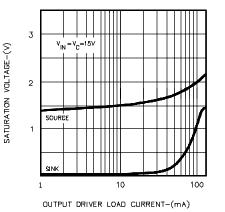


FIGURE 13. SUPPLY CURRENT VS. OUTPUT FREQUENCY









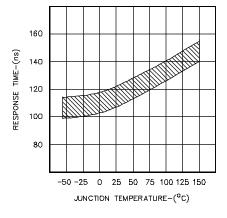


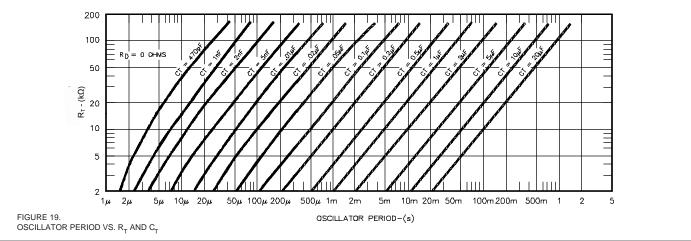
FIGURE 16. OSCILLATOR FREQUENCY TEMPERATURE STABILITY

FIGURE 17. OUTPUT DRIVER SATURATION VOLTAGE

FIGURE 18. SHUTDOWN INPUT TO DRIVER OUTPUT DELAY



CHARACTERISTIC CURVES (continued)

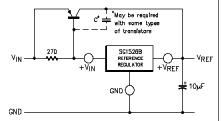


APPLICATION INFORMATION

VOLTAGE REFERENCE

The reference regulator of the SG1526B is a "band-gap" type; that is, the precision +5 volt output is derived from the very predictable base-emitter voltage of an NPN transistor. Since this is a sub-surface phenomenon, the resulting output exhibits excellent stability compared to earlier surface-breakdown Zener designs.

The reference output is stabilized at input voltages as low as +8 volts, and can provide up to 20mA of load current to external circuitry. An external PNP transistor can be used to boost the available current to many hundreds of mA. A rugged low-frequency audio-type transistor should be used, and lead lengths between the PWM and transistor should be as short as possible to minimize the risk of oscillation.



EXTENDING REFERENCE OUTPUT CURRENT

UNDERVOLTAGE LOCKOUT

The undervoltage lockout circuit protects the SG1526B and the power devices it controls from inadequate supply voltage. If +V_{IN} is too low, the circuit disables the output drivers and holds the RESET pin LOW. This prevents spurious output pulses while the control circuitry is stabilizing, and holds the soft-start timing capacitor in a discharged state.

The circuit consists of a merged bandgap reference and comparator circuit which is active when the reference voltage has risen to $2V_{BE}$ or 1.2 volts at 25°C. When the reference voltage rises to approximately +4.4 volts, the circuit enables the output drivers and releases the RESET pin, allowing a normal softstart. The comparator has 200mV of hysteresis to minimize oscillation at the trip point. When +V_{IN} to the PWM is removed and the reference drops to +4.2 volts, the undervoltage circuit pulls RESET LOW again. The soft-start capacitor is immediately discharged, and the PWM is ready for another soft-start cycle.

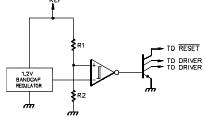


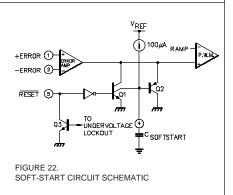
FIGURE 21. SIMPLIFIED UNDERVOLTAGE LOCKOUT

FIGURE 20

The SG1526B can operate from a +5 volt supply regulated to within ±4% by connecting the V_{REF} pin to the +V_{IN} pin.

SOFT-START CIRCUIT

The soft-start circuit protects the power transistors and rectifier diodes from high current surges during power supply turn-on. When <u>supply</u> voltage is first applied to the SG1526B, the undervoltage lockout circuit holds RESET LOW with Q3. Q1 is turned on, which holds the soft-start capacitor voltage at zero. The second collector of Q1 clamps the output of the error amplifier to ground, guaranteeing zero duty cycle at the driver outputs. When the supply voltage reaches normal operating range, RESET will go HIGH. Q1 turns off, allowing the internal 100µA current source to charge C_s. Q2 clamps the error amplifier output to 1.0 V_{BE} above the voltage on C_s. As the soft-start voltage ramps up to +5 volts, the duty cycle of the PWM linearly increases to whatever value the voltage regulation loop requires for an error null. Figure 7 gives the timing relationship between C_s ramp time to 100% duty cycle.





APPLICATION INFORMATION (continued)

DIGITAL CONTROL PORTS

The three digital control ports of the SG1526B are bidirectional. Each pin can drive TTL and 5 volt CMOS logic directly, up to a fan-out of 10 low-power Schottky gates. Each pin can also be directly driven by open-collector TTL, open-drain CMOS, and open-collector voltage comparators, fan-in is equivalent to 1 low-power Schottky gate. Each port is normally HIGH; the pin is pulled LOW to activate the particular function. Driving SYNC LOW initiates a discharge cycle in the oscillator. Pulling SHUTDOWN LOW immediately inhibits all PWM output pulses. Holding RESET LOW discharges the soft-start capacitor. The logic threshold is +1.1 volts at +25°C. Noise immunity can be gained at the expense of fan-out with an external 2k pull-up resistor to +5V.



The oscillator is programmed for frequency and dead time with three components: $R_{T} C_{T}$, and R_{D} . Two waveforms are generated: a sawtooth waveform at pin 10 for pulse width modulation, and a logic clock at pin 12. The following procedure is recommended for choosing timing values:

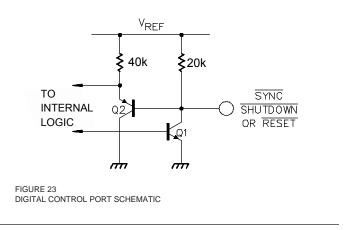
- 1. With $R_D = 0\Omega$ (pin 11 shorted to ground) select values for R_T and C_T from Figure 19 to give the desired oscillator period. Remember that the frequency at each driver output is half the oscillator frequency, and the frequency at the +V_c terminal is the same as the oscillator frequency.
- 2. If more dead time is required, select a larger value of $R_{\rm D}$ using Figure 12 as a guide. At 40 kHz dead time increases by 300 ns/ Ω .
- Increasing the dead time will cause the oscillator frequency to decrease slightly. Go back and decrease the value of R_T slightly to bring the frequency back to the nominal design value.

The SG1526B can be synchronized to an external logic clock by programming the oscillator to free-run at a frequency 10% slower than the sync frequency. A periodic LOW logic pulse approximately 0.5 μ Sec wide at the SYNC pin will then lock the oscillator to the external frequency.

ERROR AMPLIFIER

The error amplifier is a transconductance design, with an output impedance of 2 megohms. Since all voltage gain takes place at the output pin, the open-loop gain/frequency characteristics can be controlled with shunt reactance to ground. When compensated for unity-gain stability with 100 pF, the amplifier has an open-loop pole at 400 Hz.

The input connections to the error amplifier and determined by the polarity of the switching supply output voltage. For positive supplies, the common-mode voltage is +5.0 volts and the feedback connections in Figure 25A are used. With negative supplies, the common-mode voltage is ground and the feedback divider is connected between the negative output and the +5.0 volt reference voltage, as shown in Figure 25B.



Multiple devices can be synchronized together by programming one master unit for the desired frequency, and then sharing its sawtooth and clock waveforms with the slave units. All C_T terminals are connected to the C_T pin of the master, and all <u>SYNC</u> terminals are likewise connected to the <u>SYNC</u> pin of the master. Slave R_T terminals should not be left open; at least 50k should be connected from each pin to ground. Slave R_D terminals may be either left open or grounded.

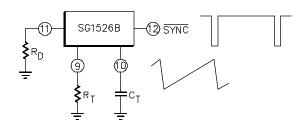


FIGURE 24. OSCILLATOR CONNECTIONS AND WAVEFORMS

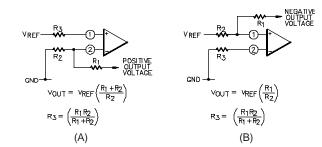


FIGURE 25. ERROR AMPLIFIER CONNECTIONS

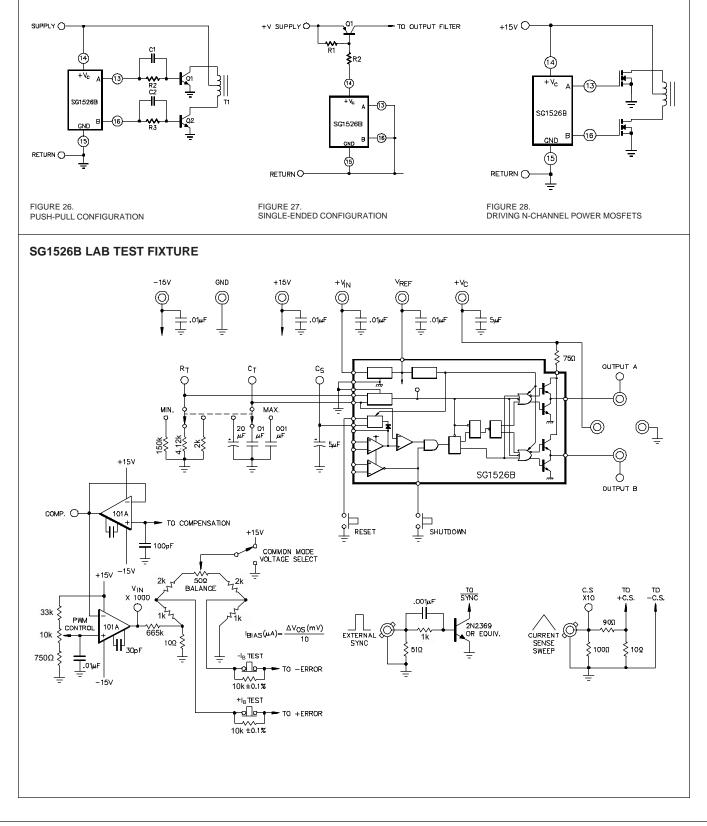


APPLICATION INFORMATION (continued)

OUTPUT DRIVERS

The totem-pole output drivers of the SG1526B are designed to source and sink 100mA continuously and 200mA peak. Loads can be driven either from the output pins 13 and 16,

or from the $+V_c$ pin, as required. Curves for the saturation voltage at these outputs as a function of load current are found in Figure 17.





CONNECTION DIAGRAMS & ORDERING INFORMATION (See Notes Below)

Package	Part No.	Ambient Temperature Range	Connection Diagram
18-PIN CERAMIC DIP J - PACKAGE	SG1526BJ-883B SG1526BJ-JAN SG1526BJ-DESC SG1526BJ SG2526BJ SG3526BJ	-55°C to 125°C -55°C to 125°C -55°C to 125°C -55°C to 125°C -25°C to 125°C -25°C to 85°C 0°C to 70°C	+ ERROR $\begin{bmatrix} 1 \\ 18 \end{bmatrix}$ V _{REF} - ERROR $\begin{bmatrix} 2 \\ 17 \end{bmatrix}$ +V _N COMPENSATION $\begin{bmatrix} 3 \\ 16 \end{bmatrix}$ OUTPUT B C _{SOFTSTART} $\begin{bmatrix} 4 \\ 15 \end{bmatrix}$ GROUND RESET $\begin{bmatrix} 5 \\ 14 \end{bmatrix}$ V _{COLLECTOR} - CURRENT SENSE $\begin{bmatrix} 6 \\ 13 \end{bmatrix}$ OUTPUT A + CURRENT SENSE $\begin{bmatrix} 7 \\ 12 \end{bmatrix}$ SYNC
18-PIN PLASTIC DIP N - PACKAGE	SG2526BN SG3526BN	-25°C to 85°C 0°C to 70°C	SHUTDOWN 8 11 R _{DEADTME} R _T 9 10 C _T N Package: RoHS Compliant / Pb-free Transition DC: 0503 N Package: RoHS / Pb-free 100% Matte Tin Lead Finish
18-PIN WIDE BODY PLASTIC SOIC DW - PACKAGE	SG2526BDW SG3526BDW	-25°C to 85°C 0°C to 70°C	+ERROR $ $ 1 18 V_{REF} -ERROR 2 17 $+V_{N}$ COMPENSATION 3 16 OUTPUT B C_{SOFISTART} 4 15 GROUND -CURRENT SENSE 6 13 OUTPUT A + CURRENT SENSE 7 12 SYNC SHUTDOWN 8 11 R _{DEADTIME} 9 10 C _T DW Package: RoHS Compliant / Pb-free Transition DC: 0516 DW Package: RoHS / Pb-free 100% Matte Tin Lead Finish
20-PIN CERAMIC LEADLESS CHIP CARRIER L- PACKAGE	SG1526BL-883B SG1526BL	-55°C to 125°C -55°C to 125°C	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$

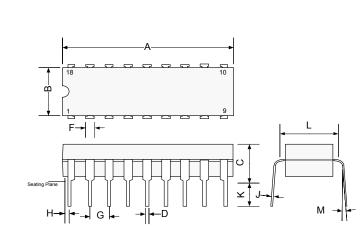
Note 1. Contact factory for JAN and DESC product availability.

Note 2. All parts are viewed from the top. Note 3. Hermetic Packages J and L use Pb37/SN63 hot solder lead finish, contact factory for availability of RoHS versions.



PACKAGE OUTLINE DIMENSIONS

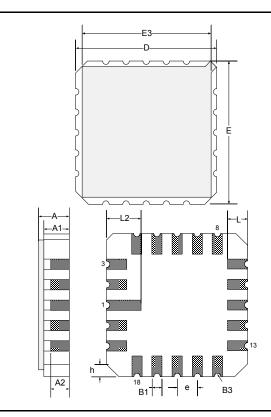
Controlling dimensions are in inches, metric equivalents are shown for general information.



	MILLIM	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
А	-	24.38	-	0.960
В	5.59	7.11	0.220	0.280
С	-	5.08	-	0.200
D	0.38	0.51	0.015	0.020
F	1.02	1.77	0.040	0.070
G	2.54	BSC	0.100	BSC
Н	-	2.03	-	0.080
J	0.20	0.38	0.008	0.015
K	3.18	5.08	0.125	0.200
L	7.37	7.87	0.290	0.310
М	-	15°	-	15°

Note: Dimensions do not include protrusions; these shall not exceed 0.155mm (0.006") on any side. Lead dimension shall not include solder coverage.

Figure 29 · J 18-Pin CERDIP Package Dimensions



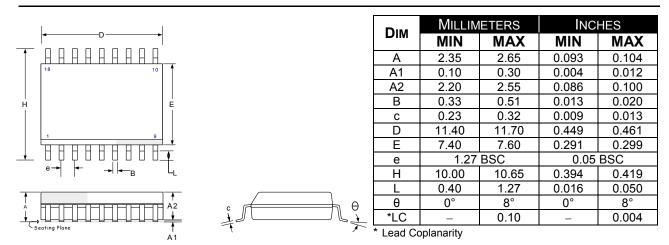
Dim	MILLIME	ETERS	INCHES		
Dim	MIN	MAX	MIN	MAX	
D/E	8.64	9.14	0.340	0.360	
E3	-	8.128	-	0.320	
е	1.270	BSC	0.050) BSC	
B1	0.635	TYP	0.02	5 TYP	
L	1.02	1.52	0.040	0.060	
Α	1.626	2.286	0.064	0.090	
h	1.016	TYP	0.04	0 TYP	
A1	1.372	1.68	0.054	0.066	
A2	-	1.168	-	0.046	
L2	1.91	2.41	0.075	0.95	
B3	0.20	3R	0.008R		

Note: All exposed metalized area shall be gold plated 60 μ-inch minimum thickness over nickel plated unless otherwise specified in purchase order.

Figure 30 · L 20-Pin Ceramic LCC Package Dimensions

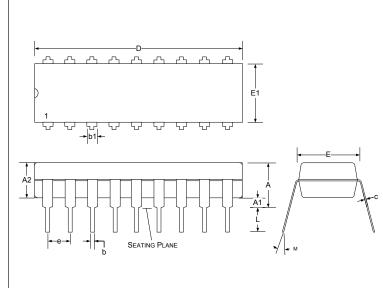


PACKAGE OUTLINE DIMENSIONS (continued)



Note: Dimensions do not include mold flash or protrusions; these shall not exceed 0.155mm (0.006") on any side. Lead dimension shall not include solder coverage.

Figure 31 · DW 18-Pin Plastic Wide-body SOIC (SOWB) Package Dimensions



Dim	MILLIMETERS		INC	HES
Dim	MIN	MAX	MIN	MAX
А		5.33		0.210
A1	0.38		0.015	
A2	3.30	Тур	0.130	О Тур
b	0.36	0.56	0.014	0.022
b1	1.14	1.78	0.045	0.070
с	0.20	0.36	0.008	0.014
D	22.35	23.34	0.880	0.920
е	2.54	BSC	0.100	BSC
E	7.62	8.26	0.300	0.325
E1	6.10	7.11	0.240	0.280
L	2.92	3.81	0.115	0.150
М	-	15°	-	15°

Note: Dimensions do not include mold flash or protrusions; these shall not exceed 0.155mm (0.006") on any side. Lead dimension shall not include solder coverage.

Figure 32 · N 18-Pin Plastic Dual Inline Package Dimensions



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